

Description

The VSM6802 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge .This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = 30V, I_D = 3.5A$

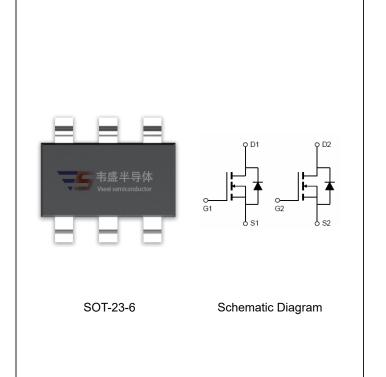
 $R_{DS(ON)}$ < 70m Ω @ V_{GS} =4.5V

 $R_{DS(ON)}$ <45m Ω @ V_{GS} =10V

- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- Battery protection
- Load switch
- Power management



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM6802-S6	VSM6802	SOT-23-6	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

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Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	VDS	30	V			
Gate-Source Voltage	Vgs	±20	V			
Drain Current-Continuous	I _D	3.5	Α			
Drain Current-Pulsed (Note 1)	I _{DM}	20	А			
Maximum Power Dissipation	P _D	1.2	W			
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C			

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	R _{θJA}	104	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit		
Off Characteristics								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	33	-	V		



Parameter	Symbol	Condition	Min	Тур	Max	Unit
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}\text{=}V_{GS},I_D\text{=}250\mu\text{A}$	1.2	1.5	2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I_D =3.5A	-	36	45	mΩ
Dialii-Source Oil-State Resistance		V_{GS} =4.5V, I_D =2A	-	59	70	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =3.5A	-	12	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	170	-	PF
Output Capacitance	Coss		-	35	-	PF
Reverse Transfer Capacitance	C _{rss}	r-1.0ivinz	-	23	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DS} =15V, R _L =4.2Ω	-	4.5	-	nS
Turn-on Rise Time	t _r		-	1.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =3 Ω	-	18.5	-	nS
Turn-Off Fall Time	t _f		-	15.5	-	nS
Total Gate Charge	Qg	V _{DS} =15V,I _D =3.5A,	-	4.0	-	nC
Gate-Source Charge	Q _{gs}		-	0.75	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	0.65	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3.5A	-	0.8	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3.5	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

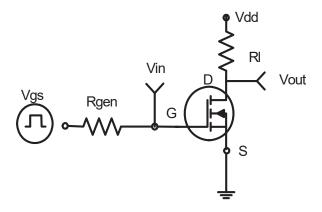
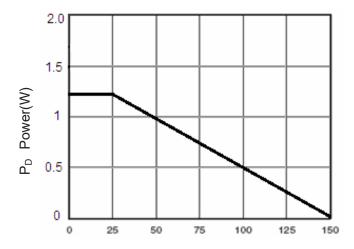


Figure 1:Switching Test Circuit



 T_J -Junction Temperature(${}^{\circ}\!\mathbb{C}$)

Figure 3 Power Dissipation

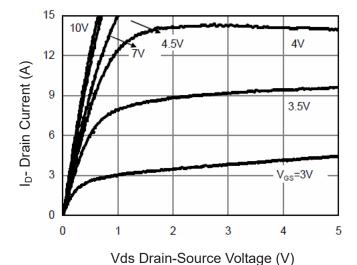


Figure 5 Output Characteristics



Figure 2:Switching Waveforms

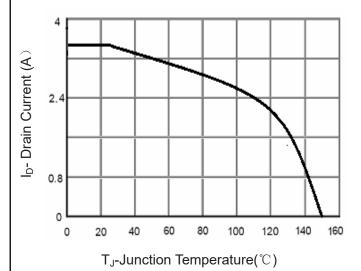


Figure 4 Drain Current

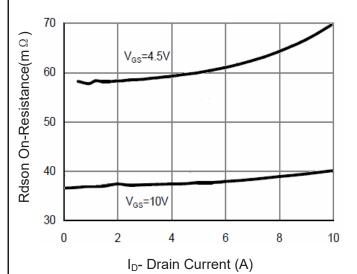


Figure 6 Drain-Source On-Resistance



Rdson On-Resistance((2))

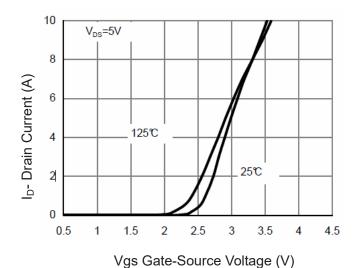
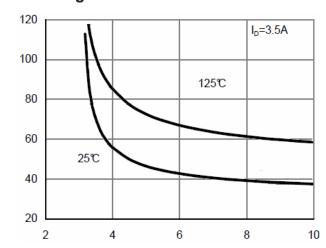


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

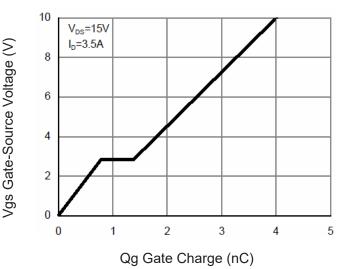


Figure 11 Gate Charge

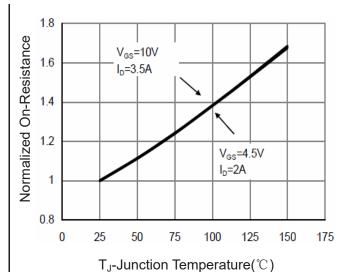


Figure 8 Drain-Source On-Resistance

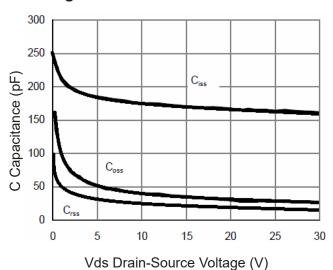


Figure 10 Capacitance vs Vds

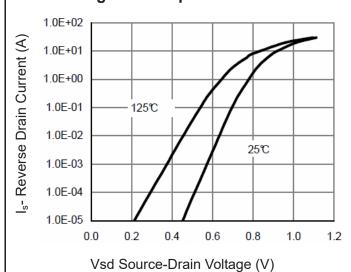


Figure 12 Source- Drain Diode Forward



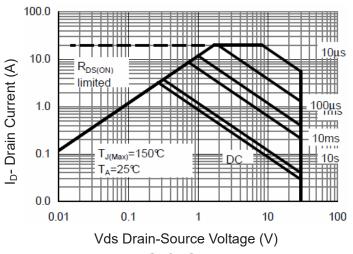


Figure 13 Safe Operation Area

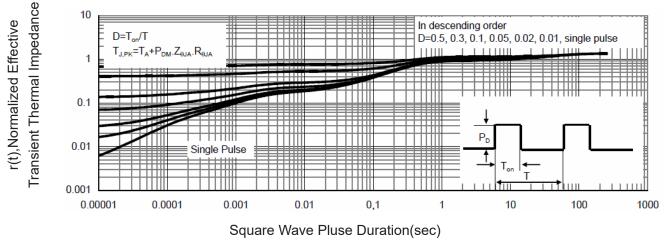


Figure 14 Normalized Maximum Transient Thermal Impedance